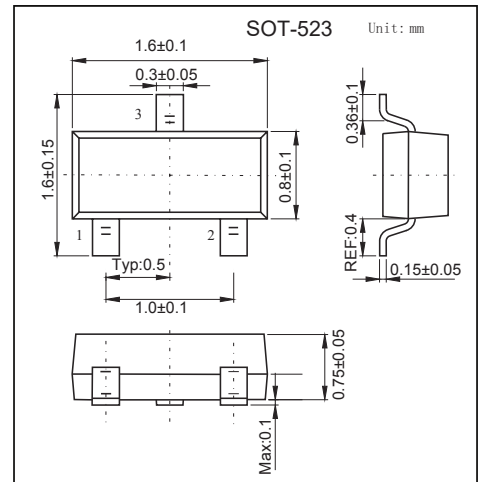


SOT-23 Plastic-Encapsulate MOSFETS
FEATURE

- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for Portable equipment
- Easily designed drive circuits
- Easy to parallel
- N-channel MOSFET

MECHANICAL DATA

- Case style:SOT-523molded plastic
- Mounting position:any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	0.1	A
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	833	°C /W
P_D	Power Dissipation	0.15	W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
30V	8Ω@4V	100mA
	13Ω@2.5V	

MOSFET ELECTRICAL CHARACTERISTICS $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0V, I_D = 10\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$			1	μA
Gate –Source leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 2	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = 3V, I_D = 100\mu A$	0.8		1.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 4V, I_D = 10mA$			8	Ω
		$V_{GS} = 2.5V, I_D = 1mA$			13	Ω
Forward Transconductance	g_{FS}	$V_{DS} = 3V, I_D = 10mA$	20			mS
Dynamic Characteristics*						
Input Capacitance	C_{iss}	$V_{DS} = 5V, V_{GS} = 0V, f = 1MHz$		13		pF
Output Capacitance	C_{oss}			9		pF
Reverse Transfer Capacitance	C_{rss}			4		pF
Switching Characteristics*						
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 5V, V_{DD} = 5V, I_D = 10mA, R_g = 10\Omega, R_L = 500\Omega,$		15		ns
Rise Time	t_r			35		ns
Turn-Off Delay Time	$t_{d(off)}$			80		ns
Fall Time	t_f			80		ns

* These parameters have no way to verify.

RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

